

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete If Known	
				Application Number	10/624,384
				Filing Date	July 22, 2003
				First Named Inventor	Leybovich
				Art Unit	1753
Examiner Name	Ver Steeg				
Sheet	1	of	3	Attorney Docket Number	020324 227P2

U.S. PATENT DOCUMENTS						class	subclass
Examiner Initials*	Cite No. ¹	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
SHV	AA	US-6,395,649	05-28-2002	Wu, Hui-Jung	438		778
SHV	AB	US-6,340,435	01-22-2002	Bjorkman et al.	216		72
	AC	US-					
	AD	US-					
	AE	US-					
	AF	US-					
	AG	US-					
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FOREIGN PATENT DOCUMENTS						
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Examiner Signature		Date Considered	March 17, 2005
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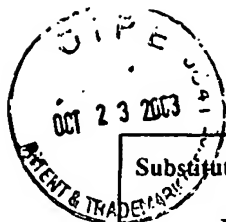
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T ²
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SHV	AU	GORBATOV, Y., VYATKIN, A. and ZINENKO, V.; A Low-Energy Fast-Atom Beam Source, Nuclear Instruments and Methods in Physics Research B55 (1991) 328-330	
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Examiner Signature		Date Considered	March 7, 2005
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